

Description

The SM6362D1RL uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

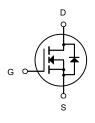
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DFN5X6-8L

General Features

V_{DS} = 30V I_D =50A

 $R_{DS(ON)}$ < 8.5m Ω V_{GS} =10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SM6362D1RL	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	30	V		
Vgs	Gate-Source Voltage	ource Voltage ±20			
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ 60			
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	А			
Ідм	Pulsed Drain Current ²	Pulsed Drain Current ² 200			
EAS	Single Pulse Avalanche Energy ³	Single Pulse Avalanche Energy ³ 36			
las	Avalanche Current	50			
P _D @T _C =25°C	Total Power Dissipation ⁴	31	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
ReJA	Thermal Resistance Junction-Ambient ¹	62	°C/W		
Rejc	Thermal Resistance Junction-Case ¹ 27		°C/W		



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	meter Conditions		Тур	Max	Units	
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V,I _D =250μA	30			V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =24V			1	μΑ	
I_{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0A			±100	nA	
$V_{\text{GS(th)}}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=250\mu A$	1.2	1.5	2.5	V	
_	Drain-Source On Resistance ²	V _{GS} =10V,I _D =30A		6.5	8.5		
R _{DS(ON)}		V _{GS} =4.5V,I _D =15A		11	14	mΩ	
G_{FS}	Forward Transconductance	V _{DS} =5V, I _D =30A		38		s	
C_{iss}	Input Capacitance	V 45V V 6V		1317	1844	pF	
C_{oss}	Output Capacitance	V_{DS} =15V, V_{GS} =0V, f =1MHz		163	228		
C_{rss}	Reverse Transfer Capacitance			131	183		
$t_{d(on)}$	Turn-On Delay Time			4.6	9.2	ns	
t _r	Rise Time	$V_{DD}=15V,I_{D}=15A,R_{L}=\Omega$		12.2	22	ns	
$t_{\sf d(off)}$	Turn-Off Delay Time	V_{GS} =15V, R_{G} =3.3 Ω		26.6	53	ns	
t_{f}	Fall Time			8	16	ns	
Q_g	Total Gate Charge			21	17.6	nC	
Q_{gs}	Gate-Source Charge	V _{GS} =4.5V,		2.35	5.9	nC	
Q_gd	Gate-Drain "Miller" Charge	V _{DS} =15V, I _D =15A		5.9	7.1	nC	
V_{SD}	Source-Drain Diode Forward Voltage ²	V _{GS} =0V,I _S =1A			1	V	
IS	Continuous Source Current1.5	VG=VD=0V,			58	А	
ISM	Pulsed Source Current2. 5	Force Current			115	Α	
trr	Reverse Recovery Time	IF=30A,		9.2			
Qrr	Reverse Recovery Charge	dI/dt=100A/¦ÌsTJ=25℃		2			

1p=30A



Typical Characteristics

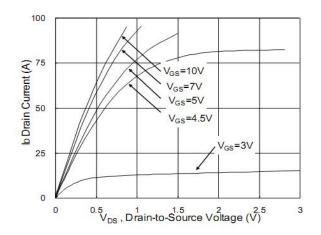
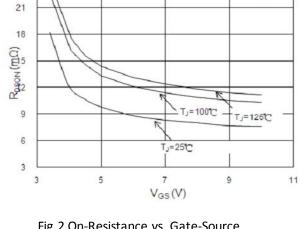


Fig. 1 Typical Output Characteristics



24

Fig. 2 On-Resistance vs. Gate-Source

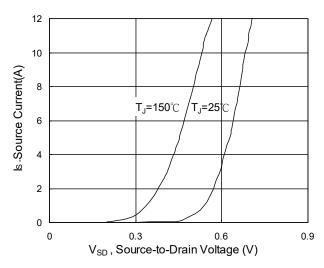


Fig.3 Forward Characteristics of reverse

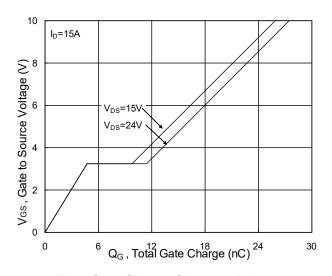


Fig.4 Gate-Charge Characteristics

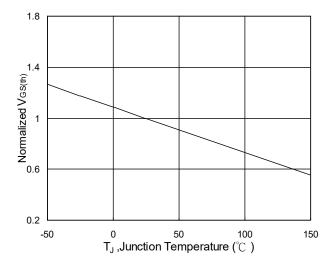


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

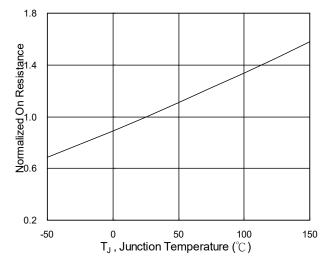
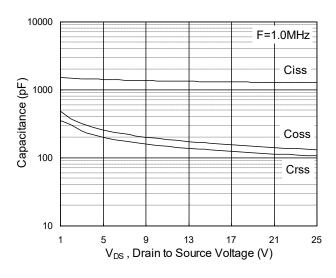


Fig.6 Normalized R_{DSON} vs. T_J





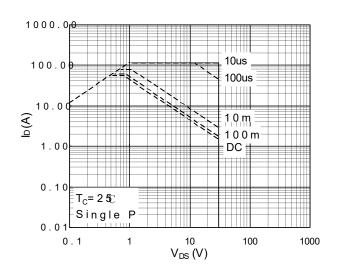
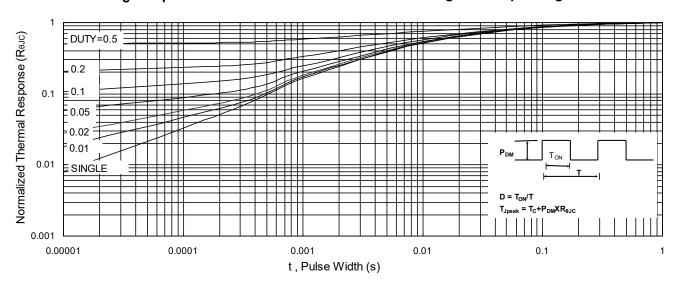
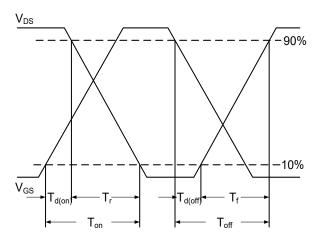


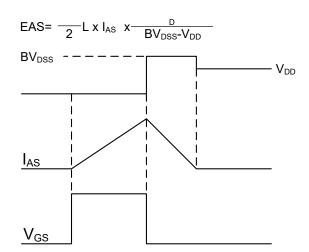
Fig.7 Capacitance

Fig.8 Safe Operating Area



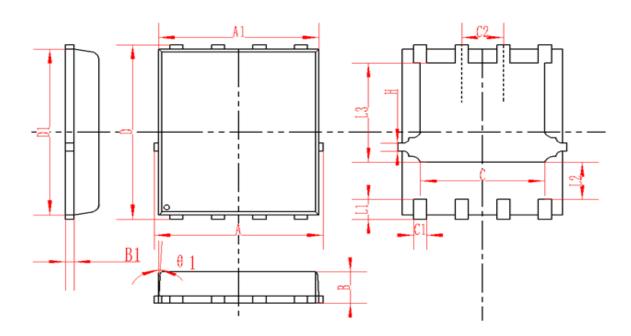








DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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